XT-02
www.oxfordplasma.de/process/inpclicp.htm

OXFORD INSTRUMENTS

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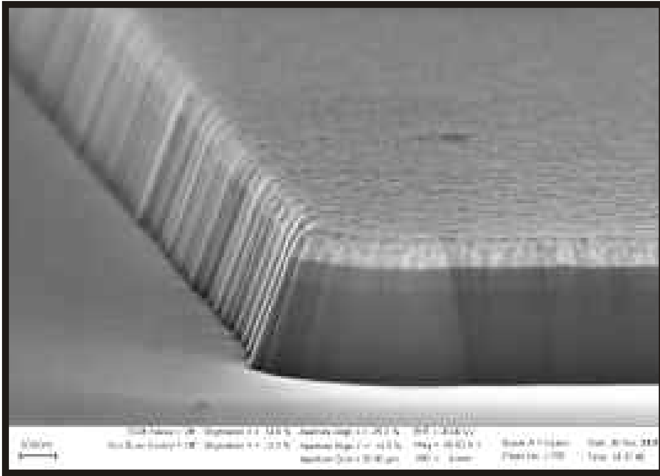
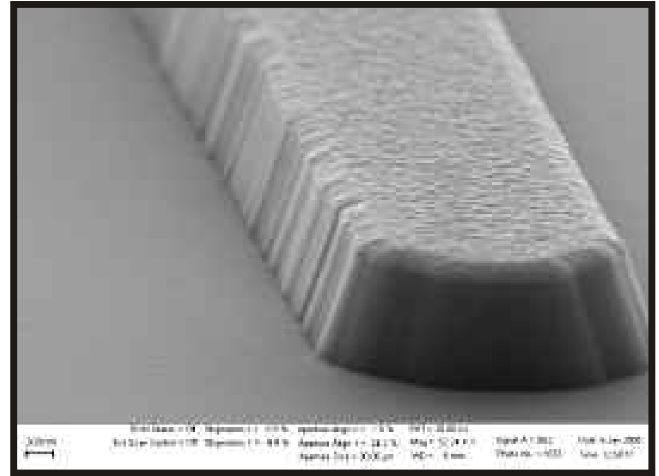
Plasmalab Data

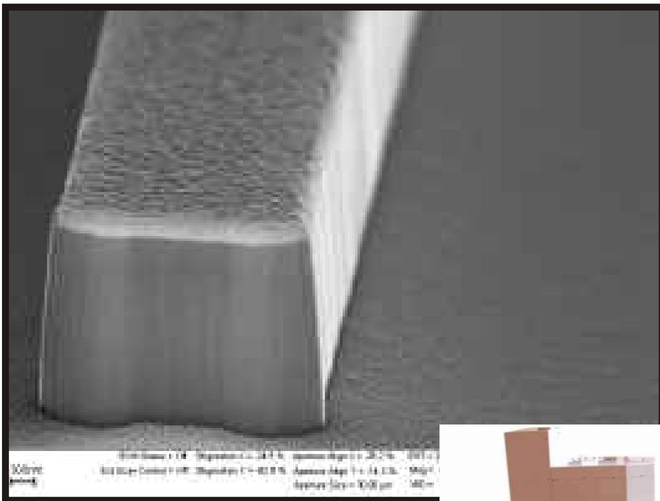
Cl2 based InP ICP Etching



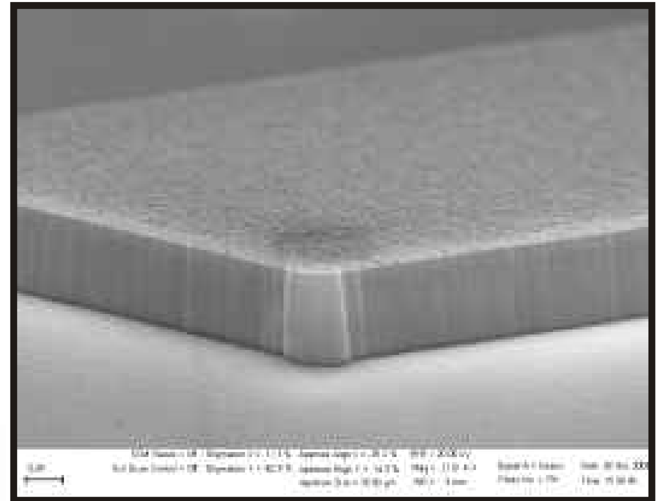
at 40 ° C



at 100 ° C



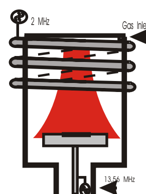
at 170 ° C



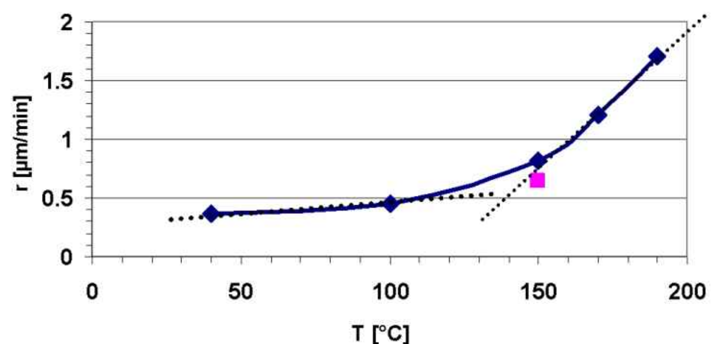
at 170 ° C

Plasmalab System 100
Plasmalab System 133

Reactive Ion Etching with ICP Source (2 or 13 MHz)
RF driven substrate electrode, Helium backside cooling



surface roughness < 5nm
low etch rate (~100nm/min) possible
The SEMs show the etch profiles at different temperatures. The Ni mask is not removed.



InP etch rate vs substrate electrode temperature

with kind permission of
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